



TO-252 Plastic-Encapsulate Transistors

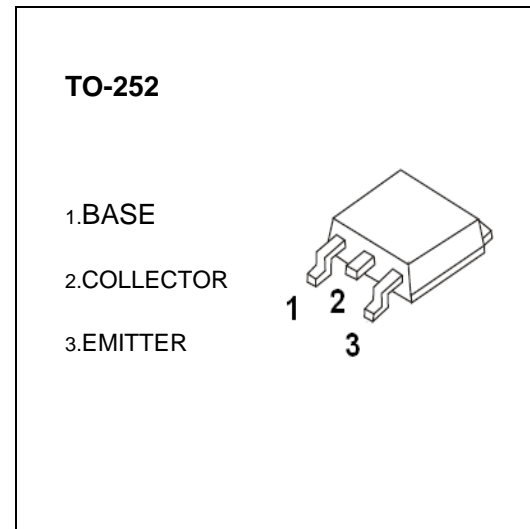
2SB1202 TRANSISTOR (PNP)

FEATURES

- Adoption of FBET,MBIT Processes
- Large Current Capacity and Wide ASO
- Low Collector-to-Emitter Saturation Voltage
- Fast Switching Speed

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector Base Voltage	-60	V
V _{CE0}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current –Continuous	-3	A
P _C	Collector Power Dissipation	1	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA, I _E =0	-60			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =-1mA, I _B =0	-50			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-100μA, I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} =-40V, I _E =0			-1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-1	μA
DC current gain	h _{FE(1)}	V _{CE} =-2V, I _C =-100mA	100		560	
	h _{FE(2)}	V _{CE} =-2V, I _C =-3A	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B =-100mA			-0.7	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA		150		MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V, I _E =0, f=1MHz		39		pF

CLASSIFICATION OF h_{FE(1)}

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560